

# SPECIFICATION

Device Name : Power MOSFET

Type Name : **2SK3270-01**

Spec. No. :

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	DATE	NAME	APPROVED	<b>Fuji Electric Co.,Ltd.</b>
DRAWN	Jun. - 4 - '98			DWG NO. <span style="float: right;">1 of 13</span>
CHECKED				

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- 1.Scope** This specifies Fuji Power MOSFET 2SK3270-01
- 2.Construction** N-Channel enhancement mode power MOSFET
- 3.Applications** for Switching
- 4.Outview** TO-220 Outview See to 5/13 page

**5.Absolute Maximum Ratings at Tc=25°C (unless otherwise specified)**

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	$V_{DS}$	60	V	
	$V_{DSX}$	30	V	$V_{GS}=-30V$
Continuous Drain Current	$I_D$	$\pm 80A$	A	
Pulsed Drain Current	$I_{DP}$	$\pm 320A$	A	
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V	
Maximum Avalanche Energy	$E_{AV}$	613	mJ	*1
Maximum Power Dissipation	$P_D$	135	W	
Operating and Storage	$T_{ch}$	150	°C	
Temperature range	$T_{stg}$	-55 to +150	°C	

\*1 L=0.13mH, Vcc=24V

**6.Electrical Characteristics at Tc=25°C (unless otherwise specified)**

**Static Ratings**

Description	Symbol	Conditions	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=1mA$ $V_{GS}=0V$	60	-	-	V
		$I_D=1mA$ $V_{GS}=-30V$	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$I_D=10mA$ $V_{DS}=V_{GS}$	2.5	3.0	3.5	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V$ $V_{GS}=0V$	-	1.0	100	$\mu A$
		$T_{ch}=125^\circ C$	-	10	500	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 30V$ $V_{DS}=0V$	-	10	100	nA
Drain-Source On-State Resistance	$R_{DS(on)}$	$I_D=40A$ $V_{GS}=10V$	-	5.0	6.5	m $\Omega$



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### Dynamic Ratings

Description	Symbol	Conditions	min.	typ.	max.	Unit
Forward Transconductance	$g_{fs}$	$I_D=40A$ $V_{DS}=10V$	25	50	-	S
Input Capacitance	$C_{iss}$	$V_{DS}=25V$	-	9000	-	pF
Output Capacitance	$C_{oss}$	$V_{GS}=0V$	-	1250	-	
Reverse Transfer Capacitance	$C_{rss}$	$f=1MHz$	-	700	-	
Turn-On Time	$t_d(on)$	$V_{cc}=30V$	-	50	-	ns
	$t_r$	$V_{GS}=10V$	-	200	-	
Turn-Off Time	$t_d(off)$	$I_D=80A$	-	150	-	
	$t_f$	$R_G=10\ \Omega$	-	135	-	

### Reverse Diode

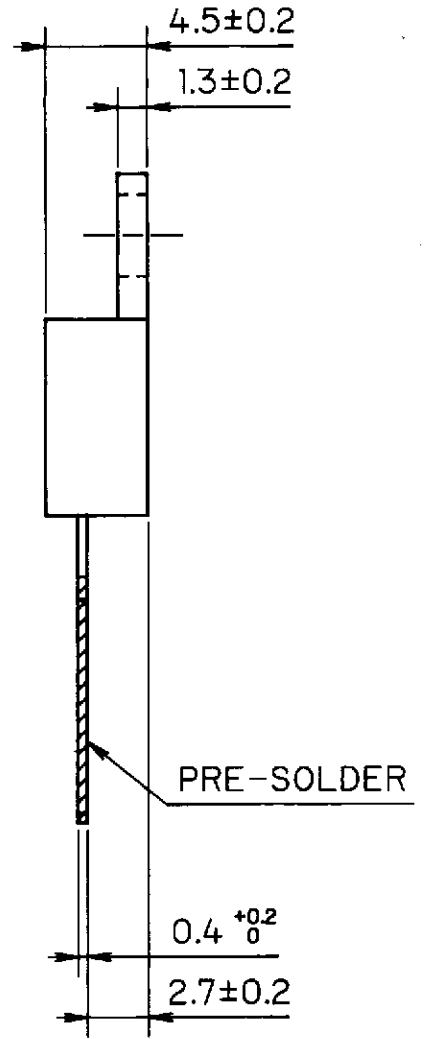
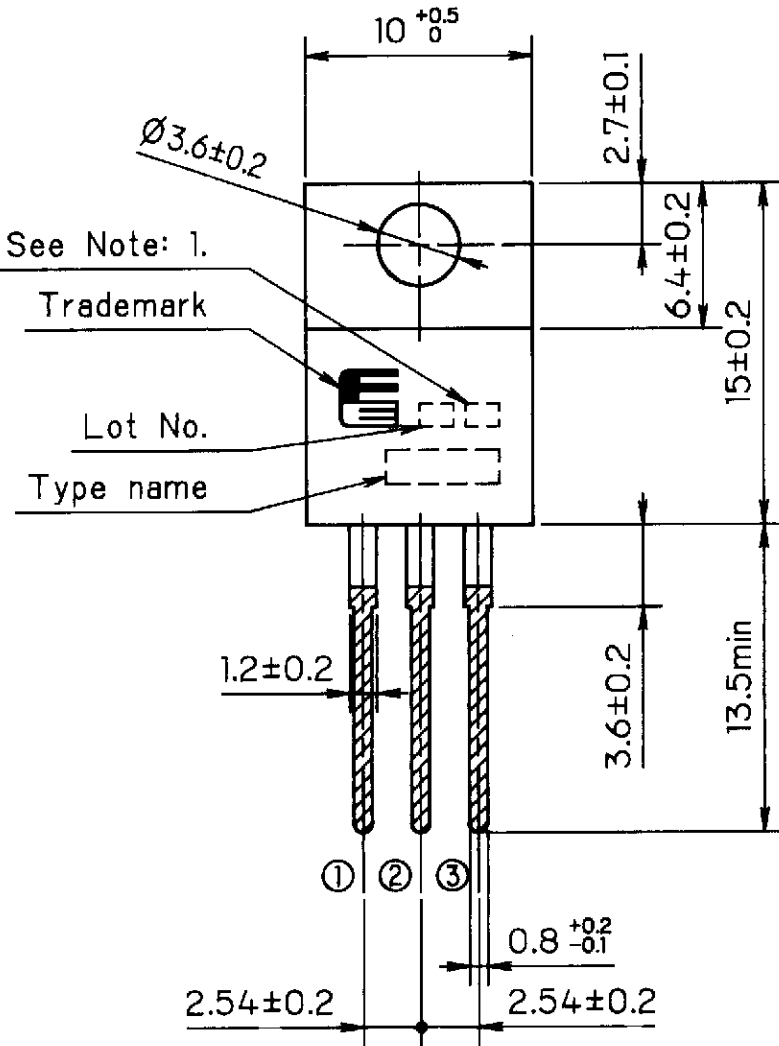
Description	Symbol	Conditions	min.	typ.	max.	Unit
Avalanche Capability	$I_{AV}$	$L=100\ \mu H$ $T_{ch}=25^\circ C$ See Fig.1 and Fig.2	80	-	-	A
Diode Forward On-Voltage	$V_{SD}$	$I_F=80A$ $V_{GS}=0V$ $T_{ch}=25^\circ C$	-	1.0	1.5	V
Reverse Recovery Time	$t_{rr}$	$I_F=50A$ $V_{GS}=0V$	-	85	-	ns
Reverse Recovery Charge	$Q_{rr}$	$-di/dt=100A/\mu s$ $T_{ch}=25^\circ C$	-	0.25	-	$\mu C$

### 7.Thermal Resistance

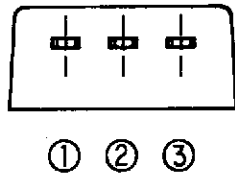
Description	Symbol	min.	typ.	max.	Unit
Channel to Case	$R_{th}(ch-c)$	-	-	0.926	$^\circ C/W$
Channel to Ambient	$R_{th}(ch-a)$	-	-	75.0	$^\circ C/W$



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CONNECTION



- ① GATE
- ② DRAIN
- ③ SOURCE

JEDEC : TO-220AB

Note: 1. Guaranteed mark of avalanche ruggedness.

DIMENSIONS ARE IN MILLIMETERS.